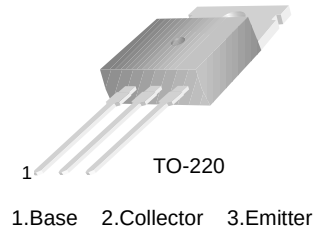


## BDW93/A/B/C

### Hammer Drivers, Audio Amplifiers Applications

- Power Darlington TR
- Complement to BDW94, BDW94A, BDW94B and BDW94C respectively



### NPN Epitaxial Silicon Transistor

#### Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

| Symbol    | Parameter                                        | Value      | Units            |
|-----------|--------------------------------------------------|------------|------------------|
| $V_{CBO}$ | Collector-Base Voltage                           |            |                  |
|           | : BDW93                                          | 45         | V                |
|           | : BDW93A                                         | 60         | V                |
|           | : BDW93B                                         | 80         | V                |
|           | : BDW93C                                         | 100        | V                |
| $V_{CEO}$ | Collector-Emitter Voltage                        |            |                  |
|           | : BDW93                                          | 45         | V                |
|           | : BDW93A                                         | 60         | V                |
|           | : BDW93B                                         | 80         | V                |
|           | : BDW93C                                         | 100        | V                |
| $I_C$     | Collector Current (DC)                           | 12         | A                |
| $I_{CP}$  | *Collector Current (Pulse)                       | 15         | A                |
| $I_B$     | Base Current                                     | 0.2        | A                |
| $P_C$     | Collector Dissipation ( $T_C=25^\circ\text{C}$ ) | 80         | W                |
| $T_J$     | Junction Temperature                             | 150        | $^\circ\text{C}$ |
| $T_{STG}$ | Storage Temperature                              | - 65 ~ 150 | $^\circ\text{C}$ |

#### Thermal Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

| Symbol          | Parameter          |                  | Value | Units              |
|-----------------|--------------------|------------------|-------|--------------------|
| $R_{\theta jc}$ | Thermal Resistance | Junction to Case | 1.5   | $^\circ\text{C/W}$ |

**Electrical Characteristics**  $T_C=25^{\circ}\text{C}$  unless otherwise noted

| Symbol          | Parameter                                                                             | Test Condition                                                                                                                        | Min.                  | Typ.       | Max.                     | Units                                                            |
|-----------------|---------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------------------------------------------------------|-----------------------|------------|--------------------------|------------------------------------------------------------------|
| $BV_{CEO(sus)}$ | * Collector-Emitter Sustaining Voltage<br>: BDW93<br>: BDW93A<br>: BDW93B<br>: BDW93C | $I_C = 100\text{mA}, I_B = 0$                                                                                                         | 45<br>60<br>80<br>100 |            |                          | V<br>V<br>V<br>V                                                 |
| $I_{CBO}$       | Collector Cut-off Current<br>: BDW93<br>: BDW93A<br>: BDW93B<br>: BDW93C              | $V_{CB} = 45\text{V}, I_E = 0$<br>$V_{CB} = 60\text{V}, I_E = 0$<br>$V_{CB} = 80\text{V}, I_E = 0$<br>$V_{CB} = 100\text{V}, I_E = 0$ |                       |            | 100<br>100<br>100<br>100 | $\mu\text{A}$<br>$\mu\text{A}$<br>$\mu\text{A}$<br>$\mu\text{A}$ |
| $I_{CEO}$       | Collector Cut-off Current<br>: BDW93<br>: BDW93A<br>: BDW93B<br>: BDW93C              | $V_{CE} = 45\text{V}, I_B = 0$<br>$V_{CE} = 60\text{V}, I_B = 0$<br>$V_{CE} = 80\text{V}, I_B = 0$<br>$V_{CE} = 100\text{V}, I_B = 0$ |                       |            | 1<br>1<br>1<br>1         | mA<br>mA<br>mA<br>mA                                             |
| $I_{EBO}$       | Emitter Cut-off Current                                                               | $V_{EB} = 5\text{V}, I_C = 0$                                                                                                         |                       |            | 2                        | mA                                                               |
| $h_{FE}$        | * DC Current Gain                                                                     | $V_{CE} = 3\text{V}, I_C = 3\text{A}$<br>$V_{CE} = 3\text{V}, I_C = 5\text{A}$<br>$V_{CE} = 3\text{V}, I_C = 10\text{A}$              | 1000<br>750<br>100    |            | 20000                    |                                                                  |
| $V_{CE(sat)}$   | * Collector-Emitter Saturation Voltage                                                | $I_C = 5\text{A}, I_B = 20\text{mA}$<br>$I_C = 10\text{A}, I_B = 100\text{mA}$                                                        |                       |            | 2<br>3                   | V<br>V                                                           |
| $V_{BE(sat)}$   | * Base-Emitter Saturation Voltage                                                     | $I_C = 5\text{A}, I_B = 20\text{mA}$<br>$I_C = 10\text{A}, I_B = 100\text{mA}$                                                        |                       |            | 2.5<br>4                 | V<br>V                                                           |
| $V_F$           | * Parallel Diode Forward Voltage                                                      | $I_F = 5\text{A}$<br>$I_F = 10\text{A}$                                                                                               |                       | 1.3<br>1.8 | 2<br>4                   | V<br>V                                                           |

\* Pulse Test:  $PW=300\mu\text{s}$ , duty Cycle =1.5% Pulsed

## Typical characteristics

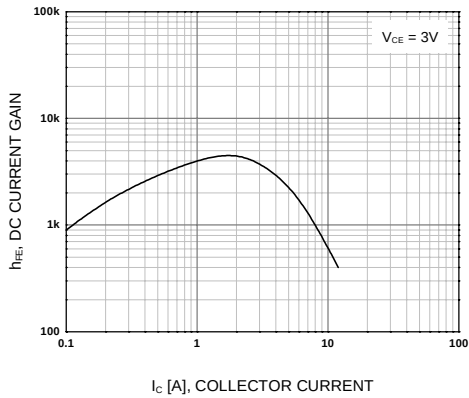


Figure 1. DC Current Gain

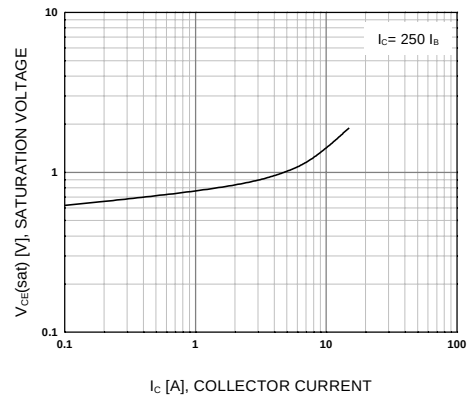


Figure 2. Collector-Emitter Saturation Voltage

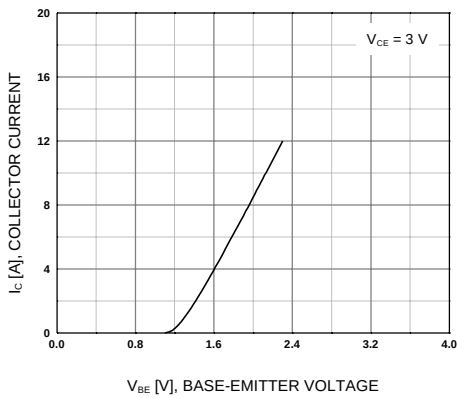


Figure 3. Base-Emitter On Voltage

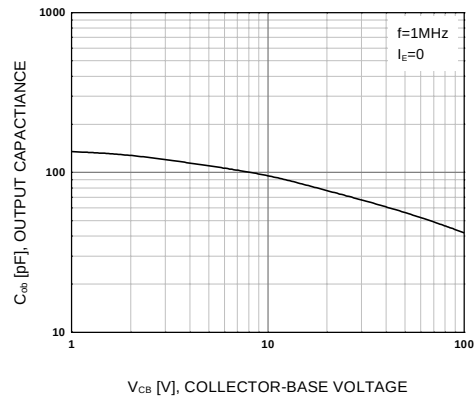


Figure 4. Collector Output Capacitance

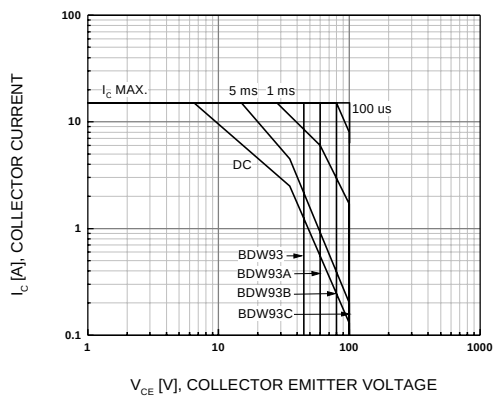


Figure 5. Safe Operating Area

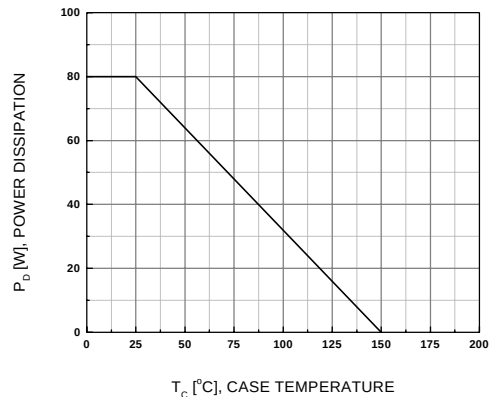
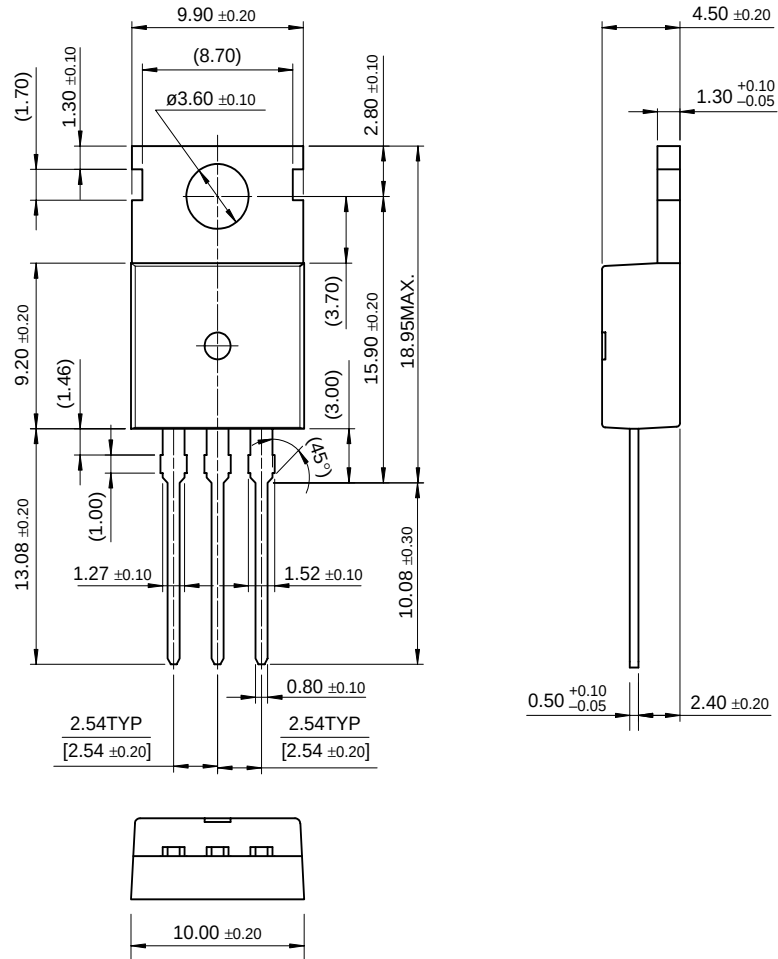


Figure 6. Power Derating

# Package Dimensions

## TO-220



Dimensions in Millimeters

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